General Description

The WST05N15 is the highest performance trench N-Channel MOSFET with extreme high cell density, which provide excellent $R_{DS(ON)}$ and gate charge for most of the synchronous buck converter applications.

The WST05N15 meet the RoHS and Green Product requirement, 100% E_{AS} guaranteed with full function reliability approved.

Product Summery

BV_{DSS}	$R_{DS(ON)}$	I_D
150V	350mΩ	1.5A

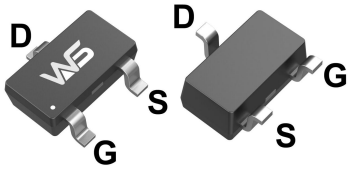
Applications

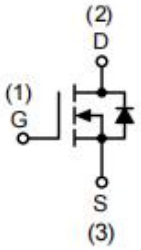
- Power Management for Industrial DC/DC Converters

Features

- 100% Final Tested.
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

SOT-23-3L Pin Configuratio





Absolute Maximum Ratings (T_A=25°C, Unless Otherwise Noted)

Symbol	Parameter		Rating	Units
V_{DS}	Drain-Source Voltage		150	V
V_{GS}	Gate-Source Voltage		±20	
I_D [7]	Continuous Drain Current	T_C=25°C	1.5	A
		T_C=100°C	0.9	
I_{DM} [3]	Pulse Drain Current		5	
P_D [2]	Power Dissipation	T_C=25°C	1.8	W
		T_C=100°C	0.4	
I_{AS} [3]	Single pulse Avalanche Current		2.3	A
E_{AS} [3]	Single pulse Avalanche Energy	L=0.3mH	2.1	mJ
T_{STG}	Storage Temperature Range		-55 to 150	°C
T_J	Operating Junction Temperature Range		-55 to 150	
$R_{\theta JA}$ [1,4]	Thermal Resistance-Junction to Ambient	t≤10s	20	°C/W
		Steady State	69	
$R_{\theta JC}$	Thermal Resistance-Junction to Case		50	

Electrical Characteristics (T_J=25°C, Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250μA	150	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=1.5A	---	350	380	mΩ
		V_{GS}=4.5V , I_D=1.5A	---	360	390	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D=250μA	1.1	1.6	2.2	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=150V , V_{GS}=0V	---	---	1.0	μA
		T_J=55°C	---	---	5.0	
I_{GSS}	Gate-Source Leakage Current	V_{DS}=0V , V_{GS}=±20V	---	---	±100	nA
g_{fs}	Forward Transconductance	V_{DS}=5V , I_D=1.5A	---	10	---	S
R_G	Gate Resistance	f=1.0MHz	1.0	2.0	3.1	Ω
Q_g	Total Gate Charge (10V)	V_{DS}=75V , V_{GS}=10V , I_D=1.5A	---	8.9	---	nC
Q_g	Total Gate Charge (4.5V)		---	5.3	---	
Q_{gs}	Gate-Source Charge		---	1.9	---	
Q_{gd}	Gate-Drain Charge		---	1.5	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DS}=75V , V_{GS}=10V , I_D=1.5A , R_L=1Ω , R_{GEN}=3Ω	---	1.9	---	ns
T_r	Rise Time		---	20	---	
$T_{d(off)}$	Turn-Off Delay Time		---	10	---	
T_f	Fall Time		---	15	---	
C_{iss}	Input Capacitance	V_{DS}=20V , V_{GS}=0V , f=1.0MHz	---	544	---	pF
C_{oss}	Output Capacitance		---	13	---	
C_{rss}	Reverse Transfer Capacitance		---	11	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
I_S [7]	Continuous Source Current		---	---	1.5	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=1.5A	---	0.7	1.0	V
t_{rr}	Reverse Recovery Time	I_F=20A , di/dt=500A/μs	---	32	---	ns
Q_{rr}	Reverse Recovery Charge		---	55	---	nC

Note:

1. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ t≤ 10s and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
2. The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
3. Single pulse width limited by junction temperature $T_{J(MAX)}$=150°C.
4. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.
5. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.
6. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150°C. The SOA curve provides a single pulse rating.
7. The maximum current rating is package limited.
8. These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.
9. The maximum current rating is silicon limited

Typical Characteristics

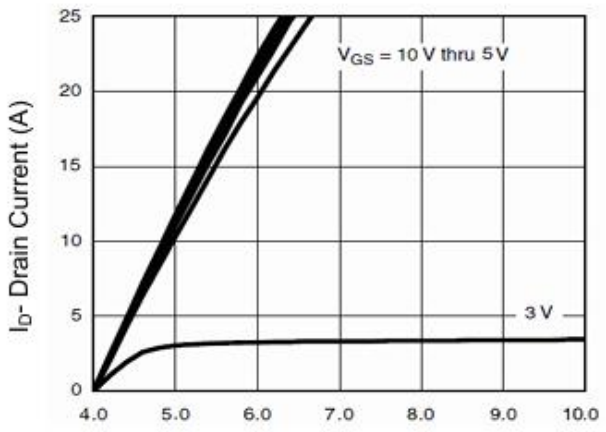


Figure 1 Output Characteristics

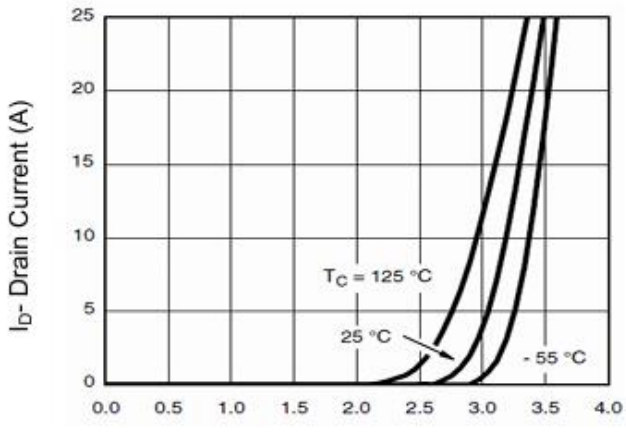


Figure 2 Transfer Characteristics

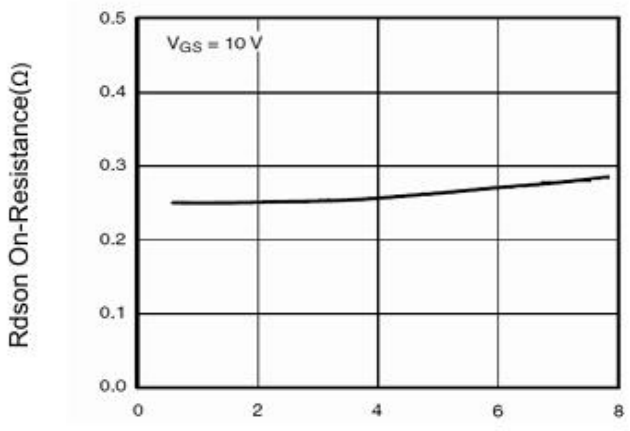


Figure 3 Rdson- Drain Current

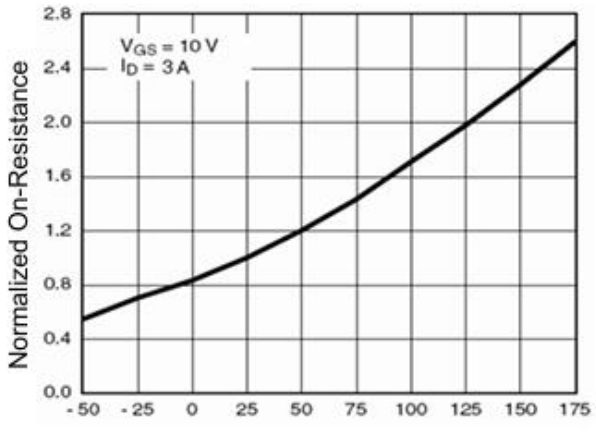


Figure 4 Rdson- Junction Temperature

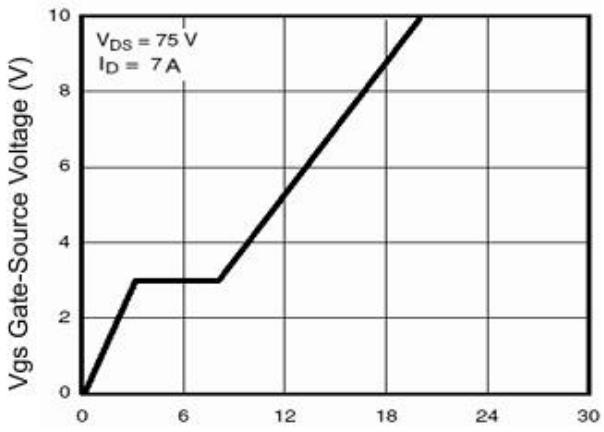


Figure 5 Gate Charge

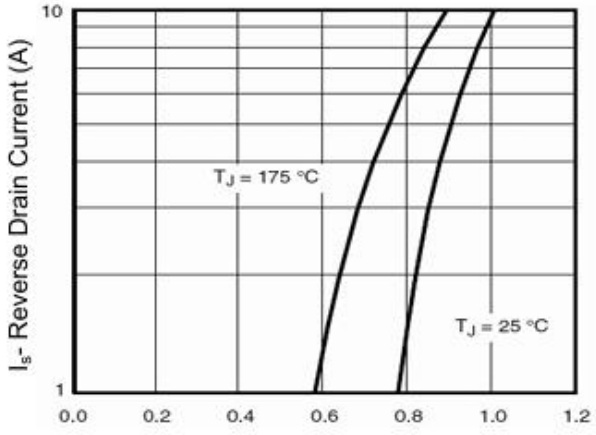


Figure 6 Source- Drain Diode Forward

Typical Characteristics (Cont.)

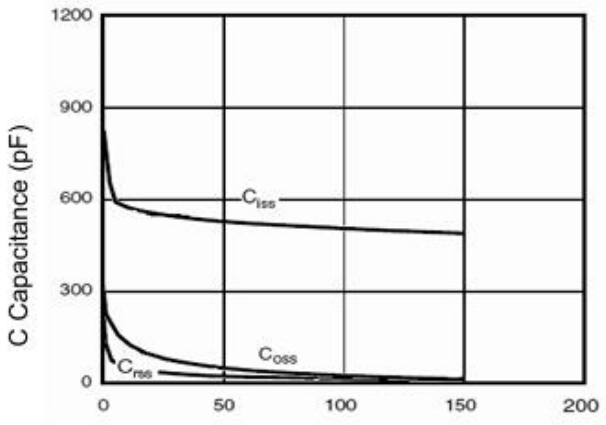


Figure 7 Capacitance vs Vds

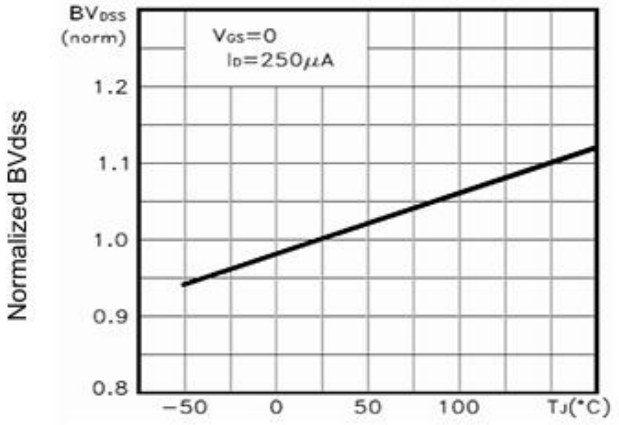


Figure 9 BV_{DSS} vs Junction Temperature

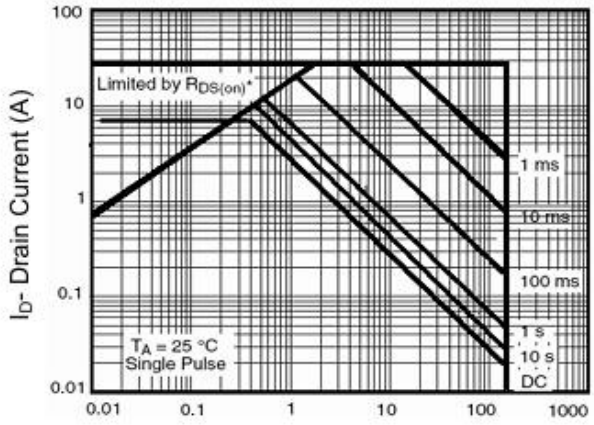


Figure 8 Safe Operation Area

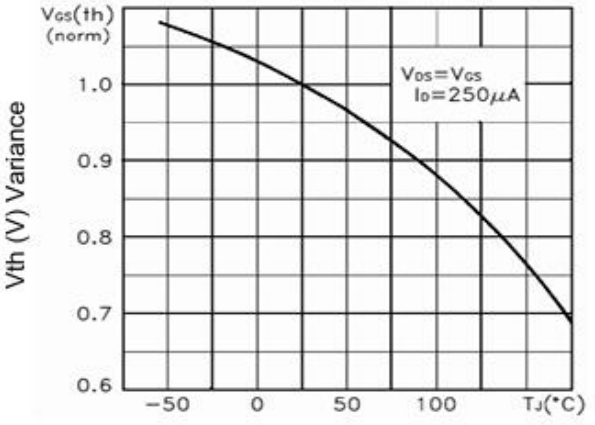


Figure 10 $V_{GS(th)}$ vs Junction Temperature

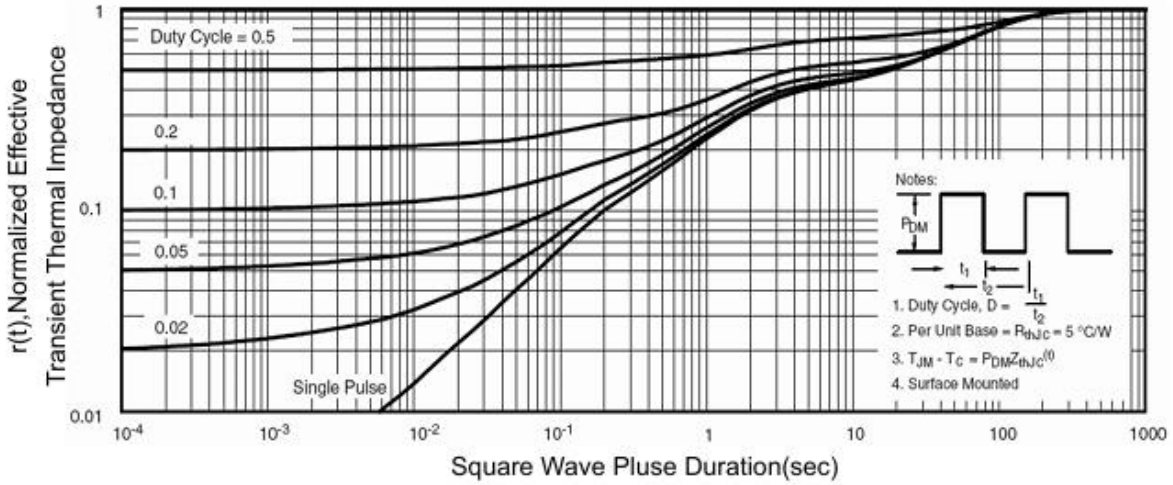
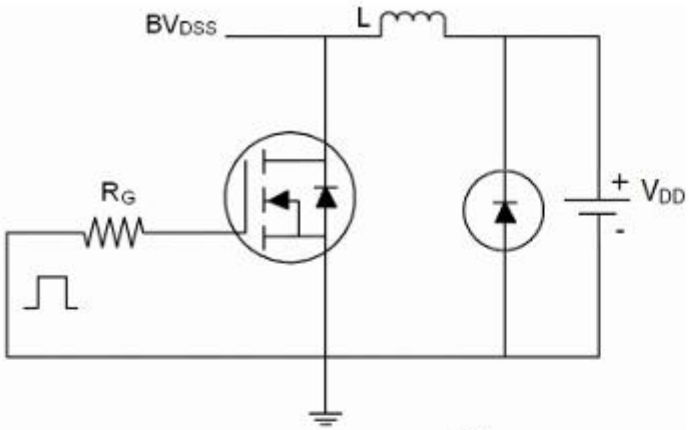


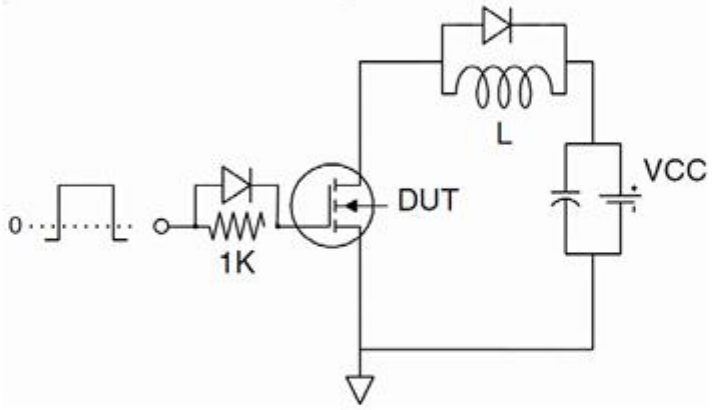
Figure 11 Normalized Maximum Transient Thermal Impedance

Fest Circuit

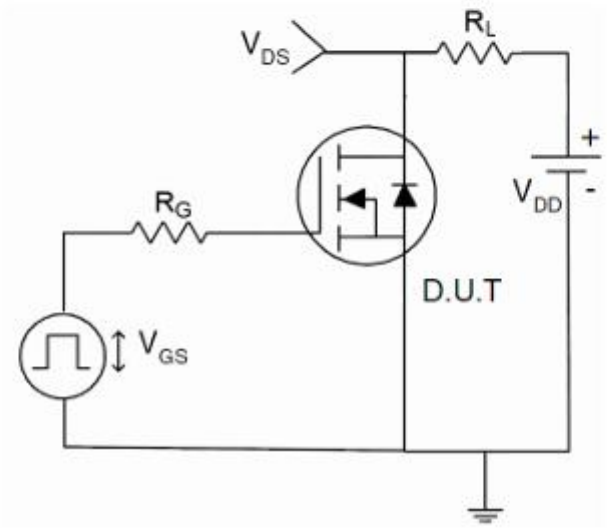
1) E_{AS} Test Circuit



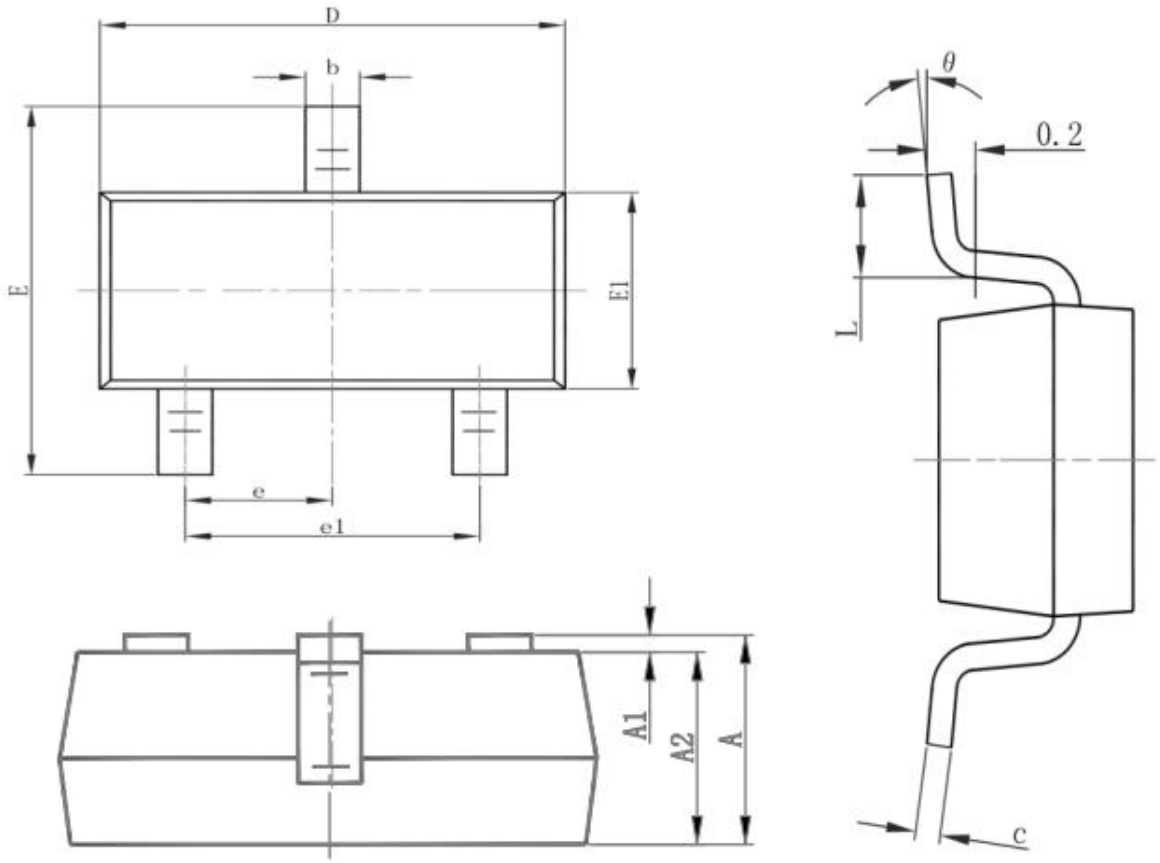
2) Gate Charge Test Circuit



3) Switch Time Test Circuit



Packaging information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

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